NSN 5961-01-070-1946

Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal
Overall Length:
1.031 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
То-94
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
1200.0 repetitive peak off-state voltage
Current Rating Per Characteristic:
110.00 amperes forward current, total rms nanoamperes
Power Rating Per Characteristic:
10.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Thread Series Designator:
Unf
Terminal Type And Quantity:
3 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig:
A110a0